TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

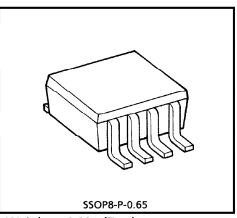
TC7WH74FU

D-TYPE FLIP FLOP WITH PRESET AND CLEAR

The TC7WH74FU is an advanced high speed CMOS D-FLIP FLOP fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The signal level applied to the D INPUT is transferred to Q OUTPUT during the positive going transition of the CK pulse.

CLR and PR are independent of the CK and are accomplished by setting the appropriate input low. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.



Weight: 0.02g (Typ.)

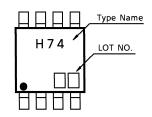
FEATURES

- High Speed f_{MAX} = 170MHz (Typ.) at V_{CC} = 5V
- Low Power Dissipation $I_{CC} = 2\mu A$ (Max.) at $Ta = 25^{\circ}C$
- High Noise Immunity ······· V_{NIH} = V_{NIL} = 28% V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······ t_{pLH}=t_{pHL}
- Wide Operation Voltage Range \dot{V}_{CC} (opr) = 2~5.5V

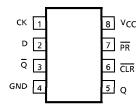
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	ΙΙΚ	- 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V _{CC} / Ground Current	lcc	± 25	mA
Power Dissipation	PD	300	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10 s)	TL	260	°C

MARKING



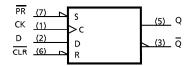
PIN ASSIGNMENT (TOP VIEW)



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LOGIC DIAGRAM



TRUTH TABLE

	INP	JTS		OUT	PUTS	FUNCTION
CLR	PR	D	CK	Q	Q	FUNCTION
L	Н	×	×	L	Н	CLEAR
Н	L	×	×	Н	L	PRESET
L	L	×	×	Н	Н	_
Н	Н	L		L	Н	_
Н	Н	Н		Н	L	_
Н	Н	×		Qn	\overline{Q}_n	NO CHANGE

x : Don't care

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~5.5	V
Input Voltage	VIN	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	٧
Operating Temperature	T _{opr}	- 40~85	°C
Innut Disc and Fall Time	dt/dv	$0\sim100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	200
Input Rise and Fall Time	at/av	$0\sim20 \ (V_{CC} = 5 \pm 0.5V)$	ns

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DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CYMPOL TEST CONDITION		Vcc	7	Γa = 25°0	C	Ta = -40~85°C		UNIT	
CHARACTERISTIC SYMBOL TE		I IESI C	TEST CONDITION VC		MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level				2.0	1.5	_	_	1.5	_	
Input Voltage	V _{IH}		_	3.0~ 5.5	V _{CC} ×0.7		_	V _{CC} ×0.7	_	V
Low-Level				2.0	_	_	0.5	_	0.5	
Input Voltage	V _{IL}		_	3.0~ 5.5	_	_	V _C C ×0.3	_	V _C C ×0.3	V
				2.0	1.9	2.0	_	1.9	_	
High Lovel	V _{OH}	V _{IN} = V _{IH}	$I_{OH} = -50\mu A$	3.0	2.9	3.0	_	2.9	_	V
High-Level Output Voltage		or V _{IL}		4.5	4.4	4.5	_	4.4	_	
Output Voltage			$I_{OH} = -4mA$	3.0	2.58	_	_	2.48	_	
			I _{OH} = -8mA	4.5	3.94	_	_	3.80	_	
			I _{OL} = 50μA	2.0		0.0	0.1	_	0.1	V
Low-Level		V.N. – V		3.0		0.0	0.1		0.1	
Output Voltage	VOL	V _{OL} V _{IN} = V _{IH} I _{OL} = 4mA I _{OL} = 8mA		4.5	_	0.0	0.1	_	0.1	
Catput Voltage			$I_{OL} = 4mA$	3.0		1	0.36	_	0.44	
			I _{OL} = 8mA			-	0.36	<u> </u>	0.44	
Input Leakage Current	IIN	V _{IN} = V _{CC} or GND		0~ 5.5			±0.1	_	± 1.0	μΑ
Quiescent Supply Current	lcc	V _{IN} = V _{CC} or GND		5.5	_	_	2.0	_	20.0	μΑ

TIMING REQUIREMENTS (Input $t_r = t_f = 3ns$)

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta =	25°C	$Ta = -40 \sim 85^{\circ}C$	UNIT
CHARACTERISTIC	3 T IVIDUL	I TEST CONDITION	V _{CC} (V)	TYP.	LIMIT	LIMIT	UNII
Minimum Pulse	t _W (L)		3.3 ± 0.3	_	6.0	7.0	ns
Width (CLOCK)	t _W (H)		5.0 ± 0.5	_	5.0	5.0	ns
Minimum Pulse	t(1)		3.3 ± 0.3	1	6.0	7.0	ns
Width (CLR, PR)	t _W (L)		5.0 ± 0.5	-	5.0	5.0	115
Minimum Set-up	+		3.3 ± 0.3	1	7.0	7.0	ns
Time	t _s		5.0 ± 0.5		5.0	5.0	115
Minimum Hold	+ ,		3.3 ± 0.3	1	0.5	0.5	ns
Time	t _h		5.0 ± 0.5	1	0.5	0.5	113
Minimum Removal	+		3.3 ± 0.3	_	5.0	5.0	ns
Time (CLR, PR)	^t rem		5.0 ± 0.5	_	3.0	3.0	115

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

CHARACTERISTIC	SYMBOL	TEST C	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT								
CHARACTERISTIC	STIVIBUL		V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT								
B			3.3 ± 0.3	15		6.7	11.9	1.0	14.0									
Propagation Delay Time	tpLH		3.3 ± 0.3	50		9.2	15.4	1.0	17.5	ne								
(CK-Q, \overline{Q})	tpHL		5.0 ± 0.5	15	_	4.6	7.3	1.0	8.5	ns								
(CK-Q, Q)	'		3.0 ± 0.3	50	_	6.1	9.3	1.0	10.5									
		<u> </u>	3.3 ± 0.3	15	_	7.6	12.3	1.0	14.5									
Propagation Delay Time	^t pLH ^t pHL		3.3 ± 0.3	50	_	10.1	15.8	1.0	18.0	ns								
$(\overline{CLR}, \overline{PR}-Q, \overline{Q})$			5.0 ± 0.5	15	_	4.8	7.7	1.0	9.0									
(CLR, PR-Q, Q)													3.0 2 0.3	50		6.3	9.7	1.0
			3.3 ± 0.3	15	80	125		70	_									
Maximum Clock	f		3.3 ± 0.5	50	50	75	_	45	_	MHz								
Frequency	fMAX		5.0 ± 0.5	15	130	170		110	_	IVITZ								
	-	3.0	3.0 ± 0.3	50	90	115	_	75	_									
Input Capacitance	CIN				_	4	10	_	10	рF								
Power Dissipation Capacitance	C _{PD}	(Note 1)			1	22	_	_	_	pF								

(Note 1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

ICC (opr) = CpD · VCC · fIN + ICC